## AMENDMENT UNDER 37 C.F.R. § 1.111 U.S. Appln. No. 09/672,776

area of from 30 to 80 m²/g, and

31,

mechanochemically polishing a metal film on said semiconductor substrate with said polishing composition.

8. (Amended) The method according to claim 6, wherein said insulating layer is made of a material selected from the group consisting of oxided silicon and nitrided silicon.

BEST AVAILABLE COPY